



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): S. MINAMI et.al.

Serial No.: 09/768,471

Filed: January 25, 2001

For: SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE  
AND METHOD OF MANUFACTURING THE SAME

Group: 2815

Examiner: B. BAUMEISTER

#15  
Amndt C  
D Smalls-Logan  
1-703

TECHNOLOGY CENTER 2600

DEC 30 2002

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Assistant Commissioner of Patents  
Washington, D. C. 20231

Dec. 23, 2002

Sir:

In response to the Office Action dated June 21, 2002, the period of response for which extension of time is requested in the attached Petition for Extension of Time, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE SUBSTITUTE SPECIFICATION:

On Page 22, please replace paragraph [0067], bridging to page 23, with the following:

[0067] Next, as shown in FIG. 17, each of side wall spacers 18 is formed on respective side walls of gate electrodes 10 and 11. Then, boron (B) ions are implanted into the n type scattering layer 3 and the n type well 4 and thereby a